

Features

- Ultra low capacitance: 0.3pF typical
- Ultra low leakage: nA level
- Low operating voltage: 5V
- Low clamping voltage
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
Air discharge: ±20kV
Contact discharge: ±20kV
 - IEC61000-4-4 (EFT) 40A (5/50ns)
 - IEC61000-4-5 (Lightning) 4A (8/20µs)
- RoHS Compliant

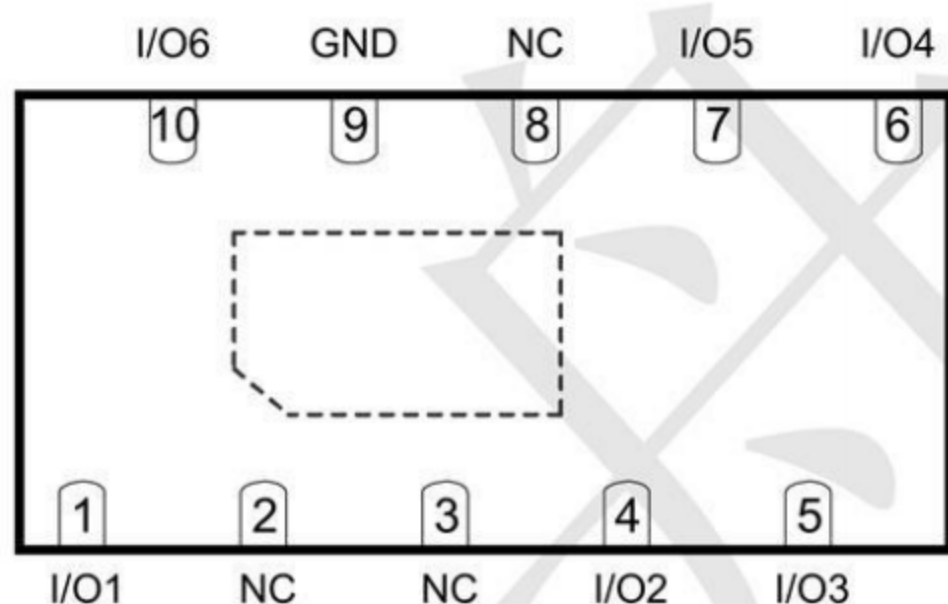
Mechanical Characteristics

- Package: DFN4120-10 (4.1×2.0×0.55mm)
- Lead Finish: NiPdAu
- Case Material: “Green” Molding Compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020

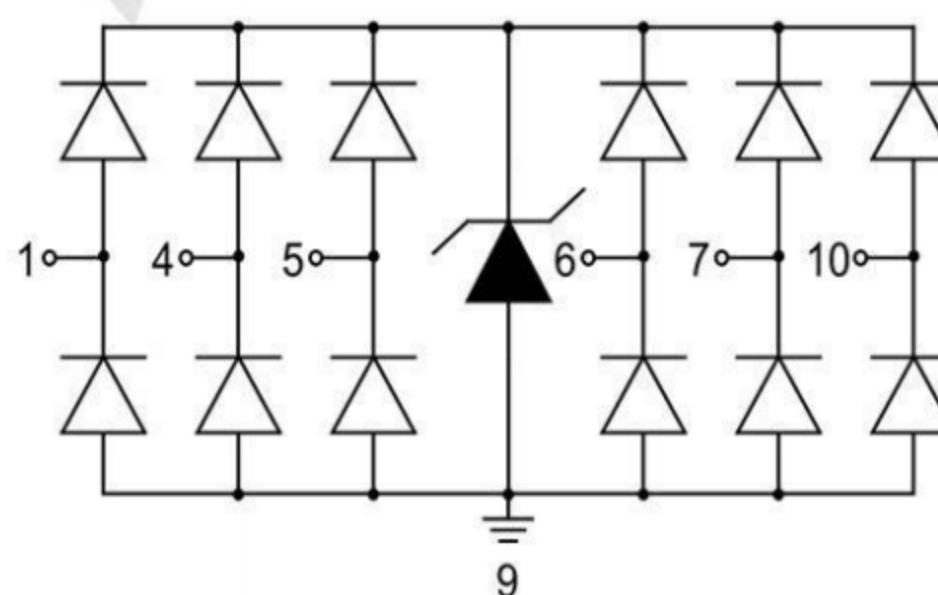
Applications

- USB 3.0
- HDMI 1.4
- High-Speed Data Lines

Dimensions and Pin Configuration



Pin Schematic



Circuit Diagram

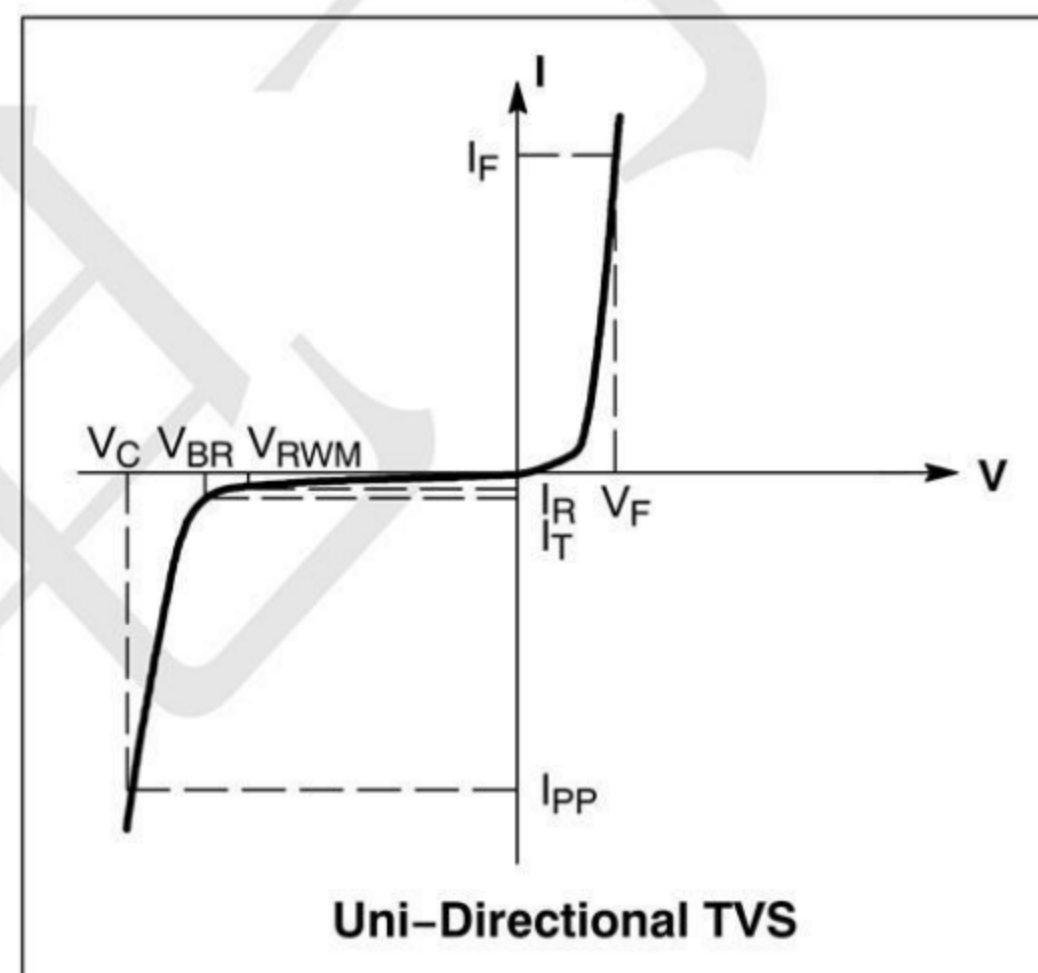
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Absolute Maximum Ratings (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20μs)	Ppk	80	W
Peak Pulse Current (8/20μs)	I _{PP}	4	A
ESD per IEC 61000-4-2 (Air)	V _{ESD}	±20	kV
ESD per IEC 61000-4-2 (Contact)		±20	
Operating Temperature Range	T _J	-55 to +125	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C

Electrical Characteristics (TA=25°C unless otherwise specified)

Symbol	Parameter
I _{PP}	Maximum Reverse Peak Pulse Current
V _C	Clamping Voltage @ I _{PP}
V _{RWM}	Working Peak Reverse Voltage
I _R	Maximum Reverse Leakage Current @ V _{RWM}
V _{BR}	Breakdown Voltage @ I _T
I _T	Test Current
I _F	Forward Current
V _F	Forward Voltage @ I _F
P _{pk}	Peak Power Dissipation
C	Capacitance @ V _R = 0 and f = 1.0 MHz



Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V _{RWM}			5	V	Any I/O pin to ground
Breakdown Voltage	V _{BR}	6			V	I _T = 1mA, any I/O pin to ground
Reverse Leakage Current	I _R			1	μA	V _{RWM} = 5V, any I/O pin to ground
Clamping Voltage	V _C			10	V	I _{PP} = 1A (8 x 20μs pulse), any I/O pin to ground
Clamping Voltage	V _C			16	V	I _{PP} = 3A (8 x 20us pulse), any I/O pin to ground
Junction Capacitance	C _J		0.3		pF	V _{CC} = 5V, V _{IN} = 2.5V, f = 1MHz, any I/O pin to ground

Typical characteristics ($T_A=25^{\circ}\text{C}$, unless otherwise noted)

Fig1. 8/20 μs Pulse Waveform

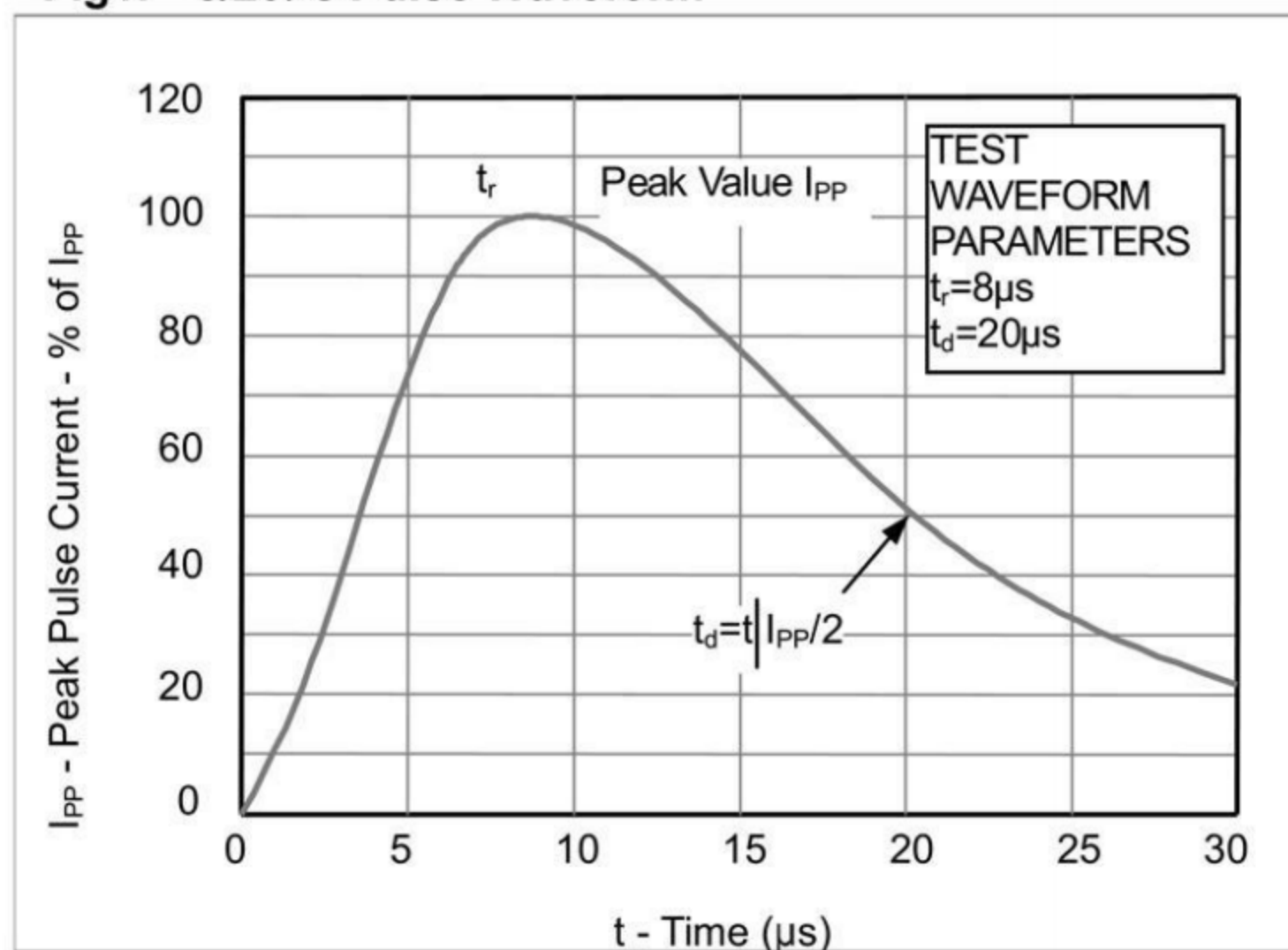


Fig2. ESD Pulse Waveform (according to IEC 61000-4-2)

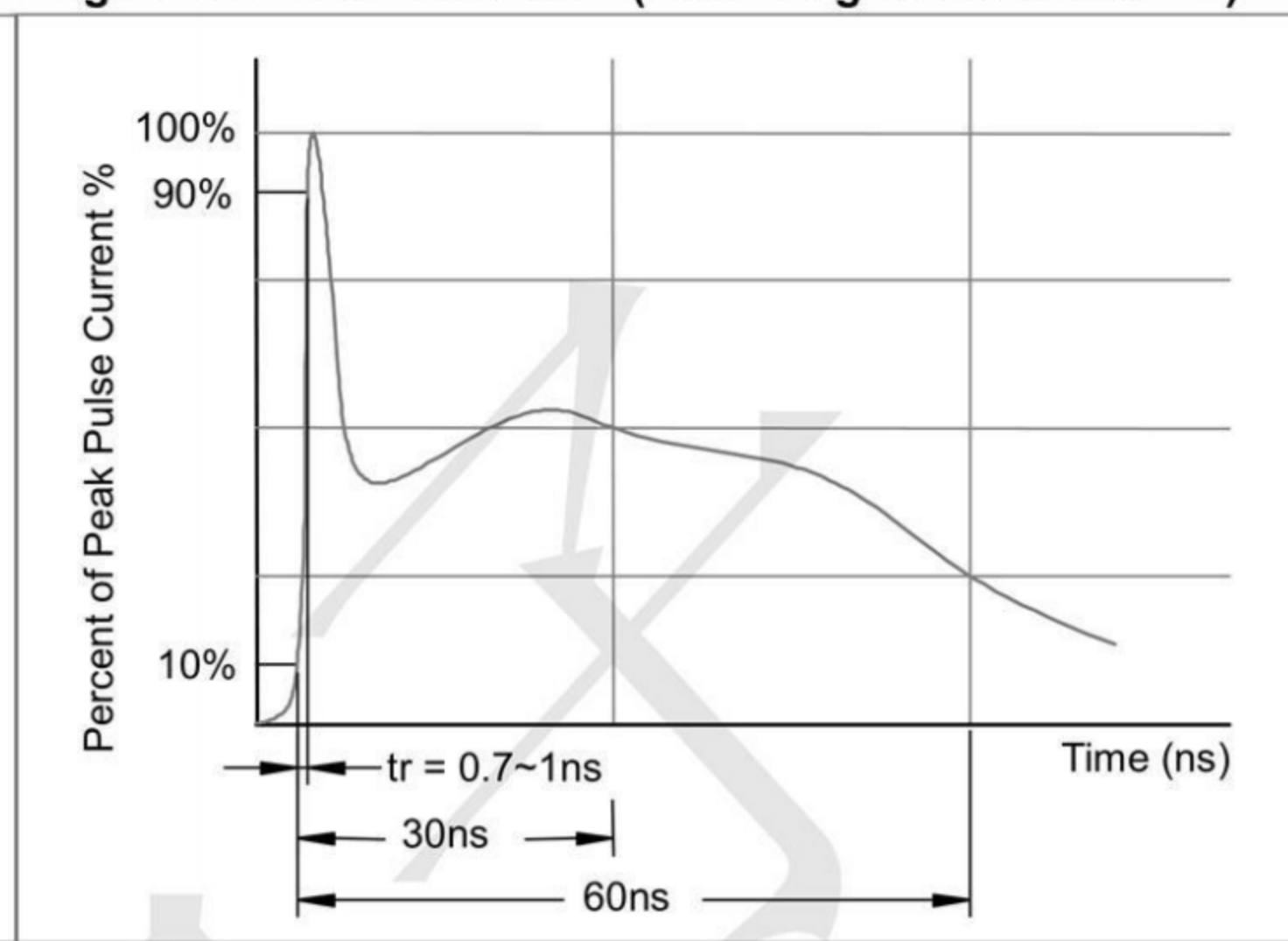
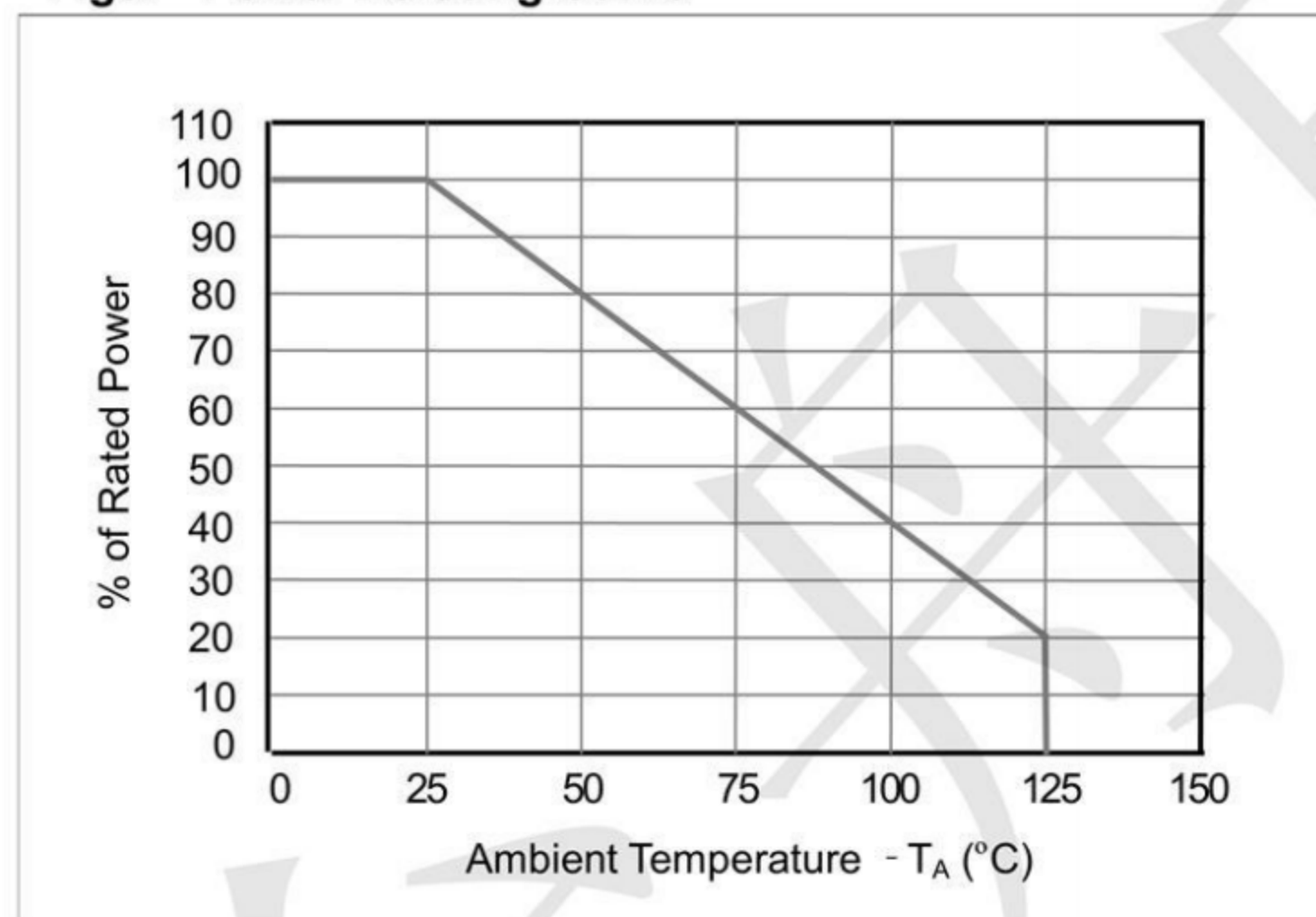
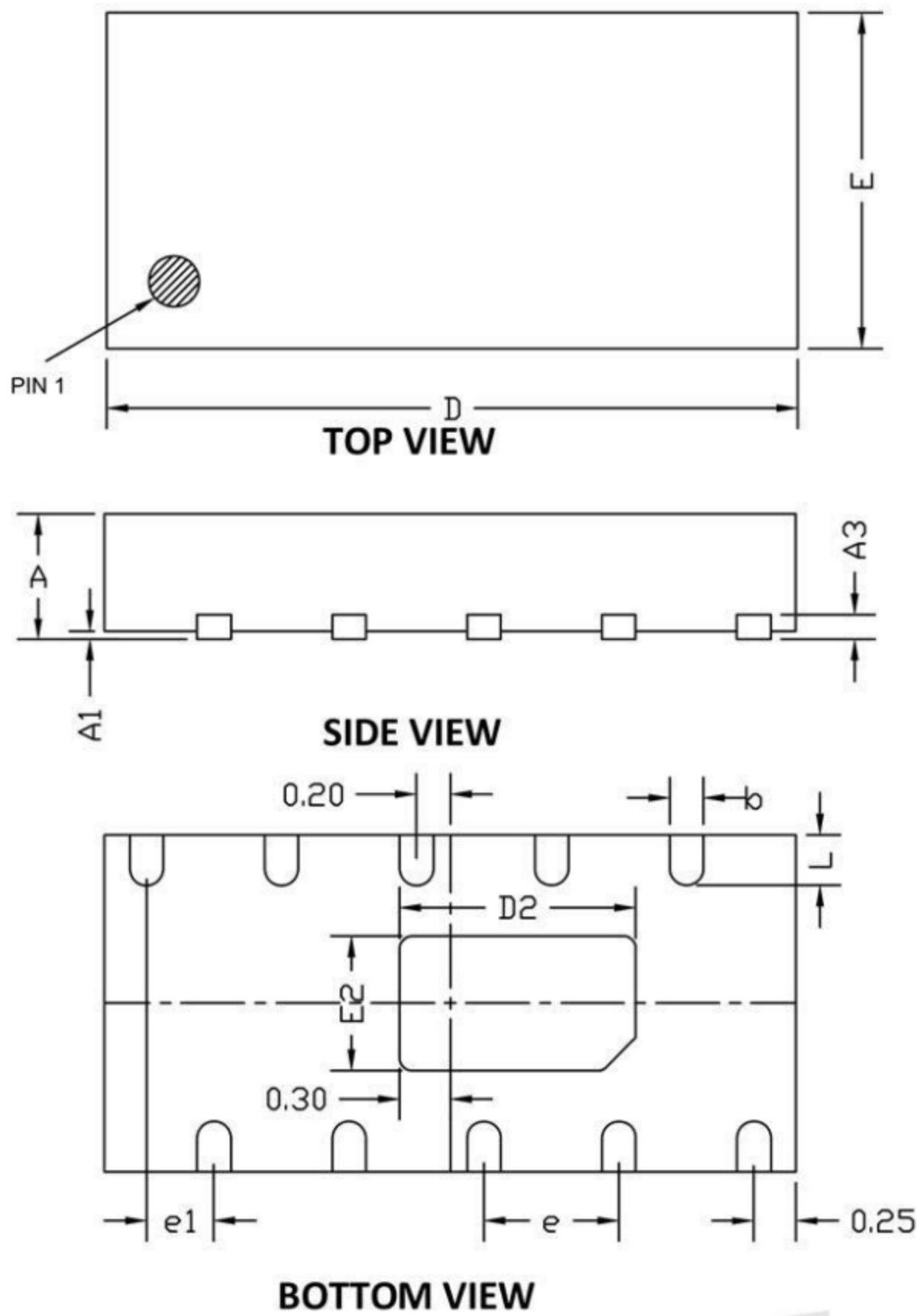


Fig3. Power Derating Curve

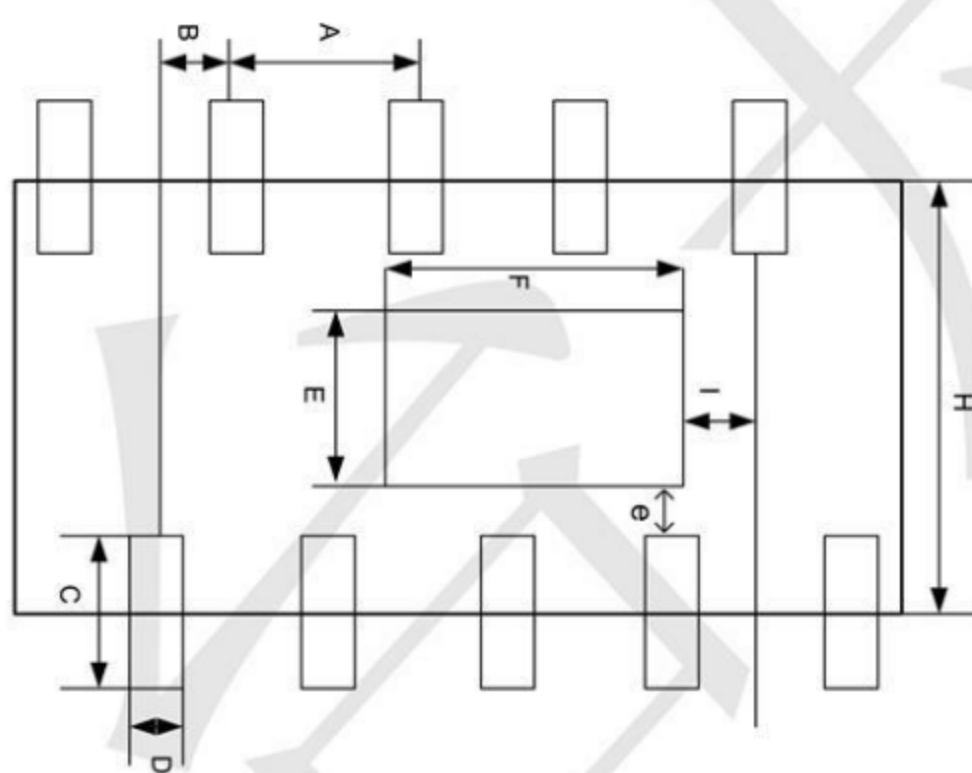


Outline Drawing - DFN4120-10



SYM	DIMENSIONS					
	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.50	0.55	0.60	0.020	0.022	0.024
A1	0.00		0.05	0.000		0.002
A3	0.15 REF			0.006 REF		
D	4.05	4.10	4.15	0.162	0.164	0.166
E	1.95	2.00	2.05	0.075	0.080	0.082
D2	1.25	1.40	1.50	0.050	0.056	0.060
E2	0.65	0.80	0.90	0.026	0.032	0.036
b	0.15	0.20	0.25	0.006	0.008	0.010
L	0.20	0.30	0.40	0.008	0.012	0.016
e1	0.40 BSC			0.016 BSC		
e	0.80 BSC			0.032 BSC		

Land Pattern - DFN4120-10



SYM	DIMENSIONS	
	MILLIMETERS	INCHES
A	0.800	0.032
B	0.400	0.016
C	0.600	0.024
D	0.200	0.008
E	0.800	0.032
F	1.400	0.056
H	2.000	0.080
I	0.300	0.012
e	0.200	0.008